

IN THE ABSTRACT OF THE DISCLOSURE:

Kindly replace the Abstract of the Disclosure with the following revised Abstract of the Disclosure:

A method for depositing a dielectric layer having a multi-layer structure on a substrate includes forming an oxidation barrier layer on a surface of a substrate; forming a plurality of dielectric layers on the oxidation barrier layer, wherein one of a plurality of additional oxidation barrier layers is disposed between each of the plurality of dielectric layers and an adjacent dielectric layer. Accordingly, a capacitor having low leakage current and high capacitance is obtained. In addition, a dielectric constant is controlled by adjusting a lattice constant so that a multi-layer structure of high dielectric constant is formed on a large substrate.

Changes in the previous paragraph are indicated by strikethrough for deletions and underlining for insertions.

A method for depositing a dielectric layer having a multi-layer structure on a substrate includes forming an ~~a first~~ oxidation barrier layer on a surface of a substrate; ~~forming a first dielectric layer on the first oxidation barrier layer; forming a second oxidation barrier layer on the first dielectric layer;~~ forming a plurality of ~~additional~~ dielectric layers on the ~~second~~ oxidation barrier layer, wherein one of a plurality of additional oxidation barrier layers is disposed between each of the plurality of ~~additional~~ dielectric layers and an adjacent ~~additional~~ dielectric layer. Accordingly, a capacitor having low leakage current and high capacitance is obtained. In addition, a dielectric constant is controlled by adjusting a lattice constant so that a multi-layer structure of high dielectric constant is formed on a large substrate.